

FTB811 TRANSISTOR (PNP)

FEATURES

- Complement to KSD1021

TO – 92M

1. EMITTER
2. COLLECTOR
3. BASE



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-30	V
V _{CEO}	Collector-Emitter Voltage	-25	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-1	A
P _C	Collector Power Dissipation	350	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	357	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -0.1mA, I _E =0	-30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-0.1mA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-30V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-1V, I _C =-0.1A	70		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1A, I _B =-0.1A			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-1A, I _B =-0.1A			-1.2	V
Collector output capacitance	C _{ob}	V _{CB} =-6V, I _E =0, f=1MHz		18		pF
Transition frequency	f _T	V _{CE} =-6V, I _C =-10mA		110		MHz

CLASSIFICATION OF h_{FE}

RANK	O	Y	G
RANGE	70-140	120-240	200-400